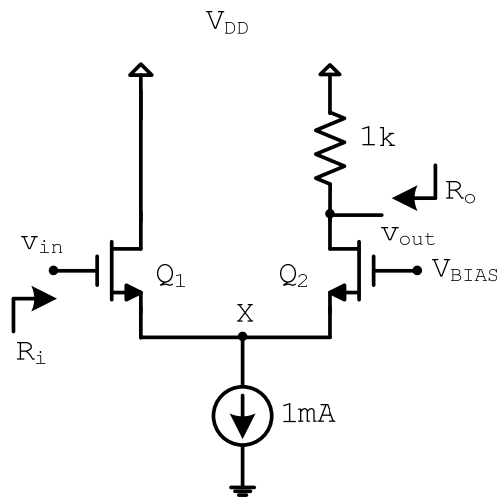


**NAME:** \_\_\_\_\_ **ID Number:** \_\_\_\_\_

*All questions are 2 points each.*

In the circuit shown below,  $V_{DD} = 3\text{ V}$  and the two MOSFETs are identical and matched with  $W = 10\text{ }\mu\text{m}$ ,  $L = 0.2\text{ }\mu\text{m}$ ,  $V_t = 0.5\text{ V}$ , and  $k'_n = 200\text{ }\mu\text{A/V}^2$ . Neglect body effect and assume  $\lambda = 0$ .



The input  $v_{IN}$  is a small sinusoidal signal superimposed on a DC level equal to  $V_{BIAS} = 1.5\text{ V}$ . The same DC  $V_{BIAS}$  (without any signal) is also applied at the gate of MOSFET  $Q_2$ .

- 1) Find the DC drain currents in  $Q_1$  and  $Q_2$ .
- 2) Find the values of  $V_{OV}$  and  $g_m$  for  $Q_1$  and  $Q_2$ .
- 3) Find the DC voltage at node X,  $V_X$ .
- 4) If the signal at node X is considered the output of the  $Q_1$  amplifier stage, determine the type of this amplifier (the first stage).
- 5) If the signal at node X is considered the input of the  $Q_2$  amplifier stage, determine the type of this amplifier (the second stage).
- 6) Find the input resistance of the amplifier  $R_i$ .

- 7) Find the output resistance of the amplifier,  $R_o$ .
- 8) Find the small-signal voltage gain of the first stage,  $v_x/v_{in}$ . Hint: Use the T model.
- 9) Find the small-signal voltage gain of the second stage  $v_{out}/v_x$ .
- 10) What is the total amplifier voltage gain  $v_{out}/v_{in}$ , *in dB*?

The capacitances in the circuit are modeled as a load capacitor  $C_L = 25$  fF that appears between the output of the amplifier and ground, and another capacitor  $C_X = 20$  fF that appears between node X and ground.

Using the OCTC method:

- 11) Find the open-circuit resistance seen by  $C_L$ .
- 12) Find the open-circuit resistance seen by  $C_X$ .
- 13) Find the 3-dB frequency for the amplifier.
- 14) Show *and label* the magnitude Bode plot for the amplifier assuming a single pole at the frequency calculated in part (13).

Assume in the following that the 1 mA current source is implemented as a simple MOSFET current mirror.

- 15) Show the circuit implementation for such a current mirror. Name the mirror transistor  $Q_3$ , and assume that it is *identical* to  $Q_1$  and  $Q_2$ .
- 16) What is the lowest possible voltage at node X to keep  $Q_3$  saturated?
- 17) What is the output resistance of the current source if, for  $Q_3$ ,  $\lambda = 0.1$  V<sup>-1</sup>?
- 18) If the voltage at node X changes by +0.1 V, find the change in current for the current source.
- 19) The 1 k $\Omega$  resistor between the drain of  $Q_2$  and the DC supply voltage is implemented as a MOSFET with gate connected to drain. Show how this MOSFET is connected.
- 20) Find the (W/L) ratio of the MOSFET in part (19) to get an equivalent small-signal resistance of 1 k $\Omega$  at a current level of 0.5 mA.